

3DD507, 3DD508, DK319**NPN Silicon Low Frequency High Power Transistor****Features:**

1. Three pins isn't connected with the cover. It could be produced according to the requirement.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for Low-speed switch, low frequency power amplify, power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+
- 5.

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications		
			3DD507	3DD508	DK319
Collector-Emitter Voltage	V _{CEO}	V	200	200	200
Emitter-Base Voltage	V _{EBO}	V	5	5	5
Max. Collector Current	I _{CM}	A	2	5	10
Max. Collector Dissipation (T _c =75°C)	P _{CM}	W	20	50	50
Junction Temperature	T _{jm}	°C	175	175	175
Storage Temperature	T _{stg}	°C	-55~+175	-55~+175	-55~+175
Emitter-Base Leakage Current	I _{EBO}	mA			
Collector-Emitter Leakage Current	I _{CEO}	mA	Max.:3.0	Max.:3.0	Max.:2.0
			V _{CE} =100V	V _{CE} =100V	V _{CE} =100V
Collector- Emitter Saturation Voltage Drop	V _{CE(sat)}	V	Max.:1.0	Max.:1.0	Max.:2.0
			I _c =1.0A, I _B =0.1A	I _c =2.5A, I _B =0.25A	I _c =2.5A, I _B =0.25A
DC Current Gain	h _{FE}		Min.:10	Min.:10	Min.:10
			V _{CE} = 5V, I _c =1A	V _{CE} = 5V, I _c =2.5A	V _{CE} = 5V, I _c =2.5A
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	V	200	200	200
			I _c =1mA	I _c =3mA	I _c =5mA
E-Base Breakdown Voltage	V _{(BR)EBO}	V	5	5	5
			I _E =0.5mA	I _E =3mA	I _E =5mA

Outline and Dimensions: